

AMENDMENTS TO THE CLAIMS:

1. (issued) A surface acoustic wave device comprising:
a LiTaO₃ substrate; and
an interdigital transducer provided on the LiTaO₃ substrate, said interdigital transducer containing as a major component at least one of Au, Ag, Ta, Mo, Cu, Ni, Cr, Zn, and W; wherein
said interdigital transducer has a normalized film thickness H/λ within a range of approximately 0.001 to approximately 0.05 so as to excite a shear horizontal wave.
2. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Au as a major component, said substrate has Euler angles of approximately (0°, 125° - 146°, 0°± 5°).
3. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Ag as a major component, said substrate has Euler angles of approximately (0°, 125° - 140°, 0°± 5°), and said normalized film thickness H/λ is within the range of approximately 0.002 to 0.05.
4. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Ta as a major component, said substrate has Euler angles of approximately (0°, 125° - 140°, 0°± 5°), and said normalized film thickness H/λ is within the range of approximately 0.002 to 0.05.
5. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Mo as a major component, said substrate has Euler

angles of approximately (0° , $125^\circ - 134^\circ$, $0^\circ \pm 5^\circ$), and said normalized film thickness H/λ is within the range of approximately 0.005 to 0.05.

6. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Cu as a major component, said substrate has Euler angles of approximately (0° , $125^\circ - 137^\circ$, $0^\circ \pm 5^\circ$), and said normalized film thickness H/λ is within the range of approximately 0.003 to 0.05.

7. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Ni as a major component, said substrate has Euler angles of approximately (0° , $125^\circ - 133^\circ$, $0^\circ \pm 5^\circ$), and said normalized film thickness H/λ is within the range of approximately 0.006 to 0.05.

8. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Cr as a major component, said substrate has Euler angles of approximately (0° , $125^\circ - 147^\circ$, $0^\circ \pm 5^\circ$), and said normalized film thickness H/λ is within the range of approximately 0.003 to 0.05.

9. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes Zn as a major component, said substrate has Euler angles of approximately (0° , $125^\circ - 138^\circ$, $0^\circ \pm 5^\circ$), and said normalized film thickness H/λ is within the range of approximately 0.003 to 0.05.

10. (issued) A surface acoustic wave device according to claim 1, wherein said interdigital transducer includes W as a major component, said substrate has Euler angles of approximately (0° , $125^\circ - 138^\circ$, $0^\circ \pm 5^\circ$), and said normalized film thickness H/λ is within the range of approximately 0.002 to 0.05.

11. (issued) A communication device including the surface acoustic wave device according to claim 1.

12. (issued) A communication device including the surface acoustic wave device according to claim 2.

13. (issued) A communication device including the surface acoustic wave device according to claim 3.

14. (issued) A communication device including the surface acoustic wave device according to claim 4.

15. (issued) A communication device including the surface acoustic wave device according to claim 5.

16. (issued) A communication device including the surface acoustic wave device according to claim 6.

17. (issued) A communication device including the surface acoustic wave device according to claim 7.

18. (issued) A communication device including the surface acoustic wave device according to claim 8.

19. (issued) A communication device including the surface acoustic wave device according to claim 9.

20. (issued) A communication device including the surface acoustic wave device according to claim 10.

21. (new) A surface acoustic wave device comprising:
a LiTaO₃ substrate; and
an interdigital transducer provided on the LiTaO₃ substrate, said interdigital
transducer containing as a major component at least one of Au, Ag, Ta, Mo, Cu, Ni, Cr,
Zn, and W; wherein
said interdigital transducer has a normalized film thickness H/λ within a range of
approximately 0.001 to approximately 0.05;
the substrate has Euler angles of approximately (0° , 136° to 147° , $0^\circ \pm 5^\circ$).

22. (new) A surface acoustic wave device according to claim 21, wherein the
major component of said interdigital transducer is Cu.

23. (new) A surface acoustic wave device according to claim 21, wherein the
substrate has Euler angles of approximately (0° , 136° to 137° , $0^\circ \pm 5^\circ$).

24. (new) A surface acoustic wave device according to claim 21, wherein the
substrate has Euler angles of approximately (0° , 136.5° , $0^\circ \pm 5^\circ$).

25. (new) A surface acoustic wave device according to claim 21, wherein the
normalized thickness H/λ is within a range of approximately 0.03 to approximately 0.05.

26. (new) A surface acoustic wave device according to claim 21, wherein the
normalized thickness H/λ is approximately 0.04.

27. (new) A surface acoustic wave device according to claim 21, wherein the major component is Cu;

the normalized thickness H/λ is within a range of approximately 0.03 to approximately 0.05; and

the substrate has Euler angles of approximately (0° , 136° to 137° , $0^\circ \pm 5^\circ$).

28. (new) A surface acoustic wave device according to claim 21, wherein the major component is Cu;

the normalized thickness H/λ is approximately 0.04; and

the substrate has Euler angles of approximately (0° , 136° to 137° , $0^\circ \pm 5^\circ$).

29. (new) A surface acoustic wave device according to claim 21, wherein the major component is Cu;

the normalized thickness H/λ is within a range of approximately 0.03 to approximately 0.05; and

the substrate has Euler angles of approximately (0° , 136.5° , $0^\circ \pm 5^\circ$).

30. (new) A surface acoustic wave device according to claim 21, wherein the major component is Cu;

the normalized thickness H/λ is approximately 0.04; and

the substrate has Euler angles of approximately (0° , 136.5° , $0^\circ \pm 5^\circ$).

31. (new) A surface acoustic wave device according to claim 21, wherein the major component is Cu; and

the substrate has Euler angles of approximately (0° , 136° to 137° , $0^\circ \pm 5^\circ$).

32. (new) A surface acoustic wave device according to claim 21, wherein the major component is Cu; and

the substrate has Euler angles of approximately (0°, 136.5°, 0°±5°).